

MMFTN3406

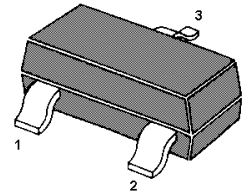
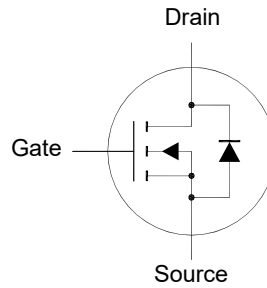
N-Channel Enhancement Mode Power MOSFET

Features

- Surface-mounted package

Applications

- Portable appliances
- Battery management



1. Gate 2. Source 3. Drain
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$ unless otherwise specified)

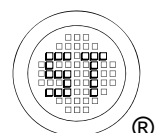
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	3.6	A
Drain Current - Pulsed ¹⁾	I_{DM}	15	A
Power Dissipation ²⁾	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Resistance Ratings

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient ²⁾	$R_{\theta JA}$	90	$^\circ\text{C}/\text{W}$

¹⁾ Pulse Test: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{j(\text{MAX})} = 150^\circ\text{C}$.

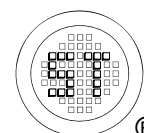
²⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air, $t \leq 10 \text{ s}$.



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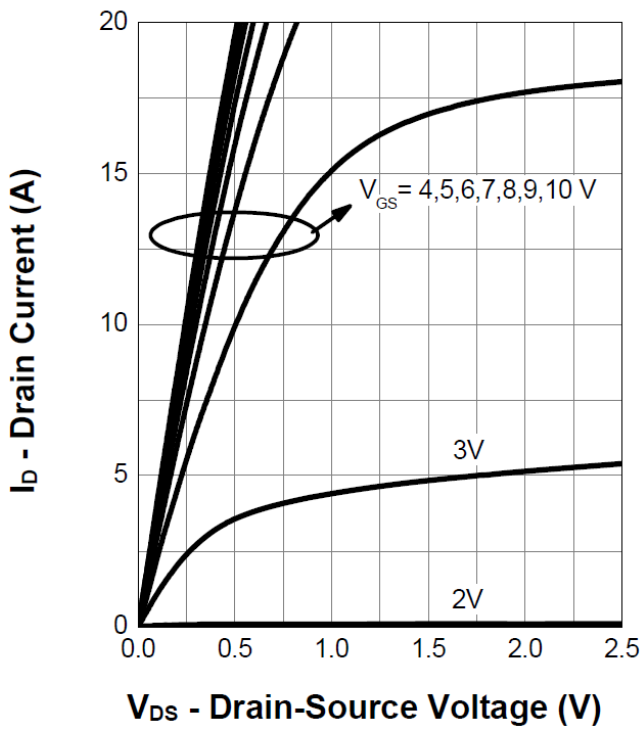
Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 250 \mu\text{A}$	BV_{DSS}	30	-	-	V
Drain-Source Leakage Current at $V_{DS} = 24 \text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current at $V_{GS} = \pm 20 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	$V_{GS(th)}$	1	-	2	V
Drain-Source On-State Resistance at $V_{GS} = 10 \text{ V}, I_D = 3.6 \text{ A}$ at $V_{GS} = 4.5 \text{ V}, I_D = 2.8 \text{ A}$	$R_{DS(on)}$	- -	- -	65 105	$\text{m}\Omega$
DYNAMIC PARAMETERS					
Input Capacitance at $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{iss}	-	363	-	pF
Output Capacitance at $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{oss}	-	49	-	pF
Reverse Transfer Capacitance at $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{rss}	-	39	-	pF
Total Gate Charge at $V_{DS} = 15 \text{ V}, I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}$ at $V_{DS} = 15 \text{ V}, I_D = 3 \text{ A}, V_{GS} = 4.5 \text{ V}$	Q_g	- -	7.2 3.4	- -	nC
Gate Source Charge at $V_{DS} = 15 \text{ V}, I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}$	Q_{gs}	-	1.7	-	nC
Gate Drain Charge at $V_{DS} = 15 \text{ V}, I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}$	Q_{gd}	-	1	-	nC
Turn-On Delay Time at $V_{DS} = 15 \text{ V}, I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}, R_G = 3.9 \Omega$	$t_{d(on)}$	-	3.9	-	ns
Turn-On Rise Time at $V_{DS} = 15 \text{ V}, I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}, R_G = 3.9 \Omega$	t_r	-	8.8	-	ns
Turn-Off Delay Time at $V_{DS} = 15 \text{ V}, I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}, R_G = 3.9 \Omega$	$t_{d(off)}$	-	10	-	ns
Turn-Off Fall Time at $V_{DS} = 15 \text{ V}, I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}, R_G = 3.9 \Omega$	t_f	-	3.7	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $I_S = 1.25 \text{ A}$	V_{SD}	-	-	1.3	V
Body-Diode Continuous Current	I_S	-	-	3.6	A
Body Diode Reverse Recovery Time at $I_S = 3 \text{ A}, di/dt = 100 \text{ A} / \mu\text{s}$	t_{rr}	-	5.9	-	nS
Body Diode Reverse Recovery Charge at $I_S = 3 \text{ A}, di/dt = 100 \text{ A} / \mu\text{s}$	Q_{rr}	-	2.4	-	nC

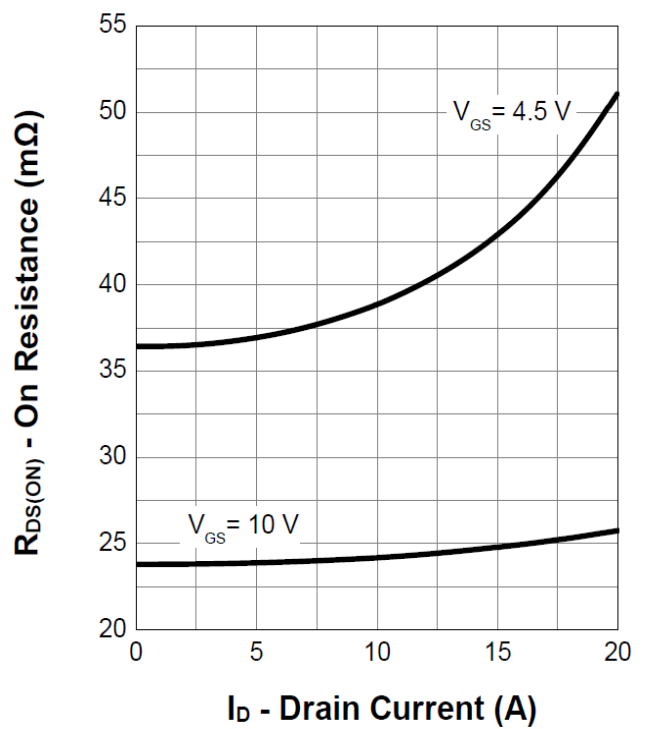


Electrical Characteristics Curves

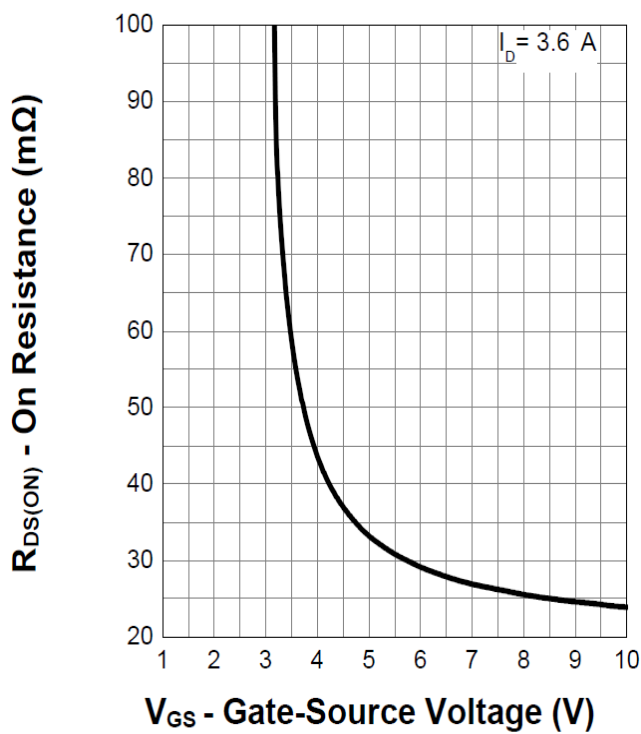
Output Characteristics



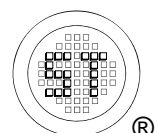
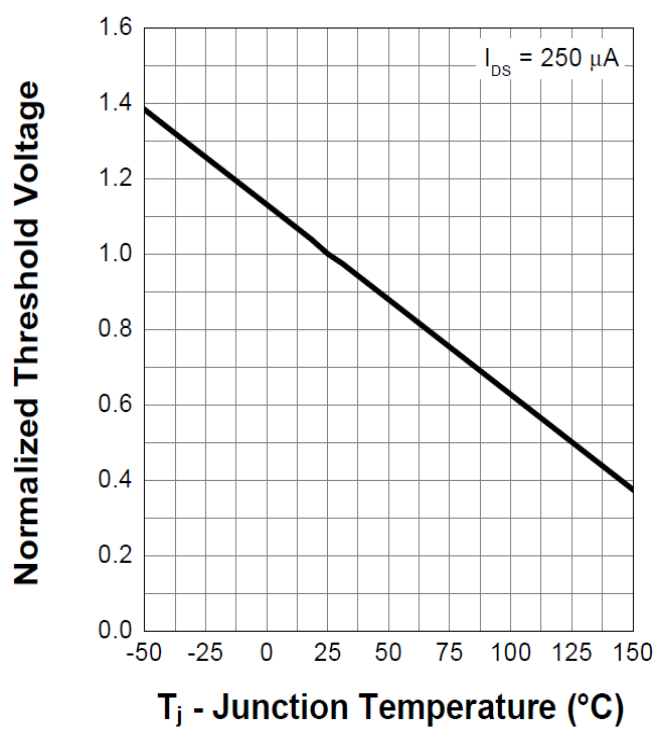
On Resistance



Transfer Characteristics

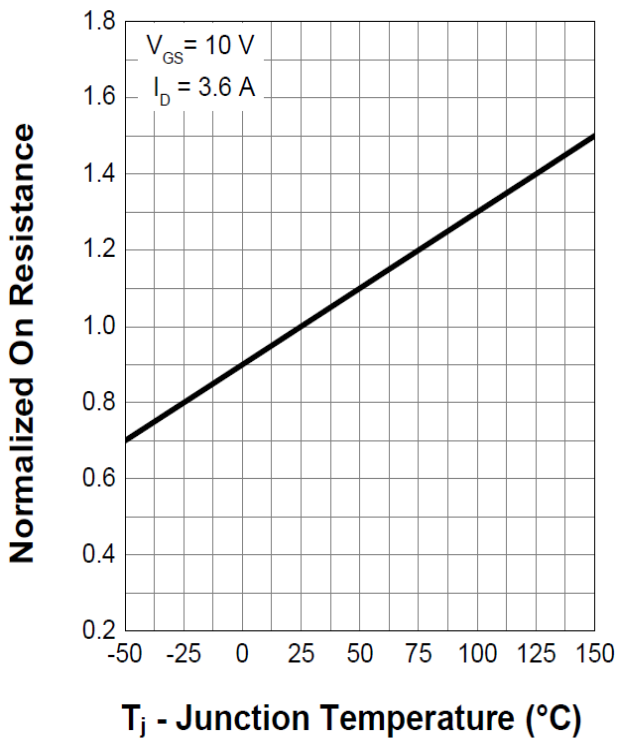


Normalized Threshold Voltage

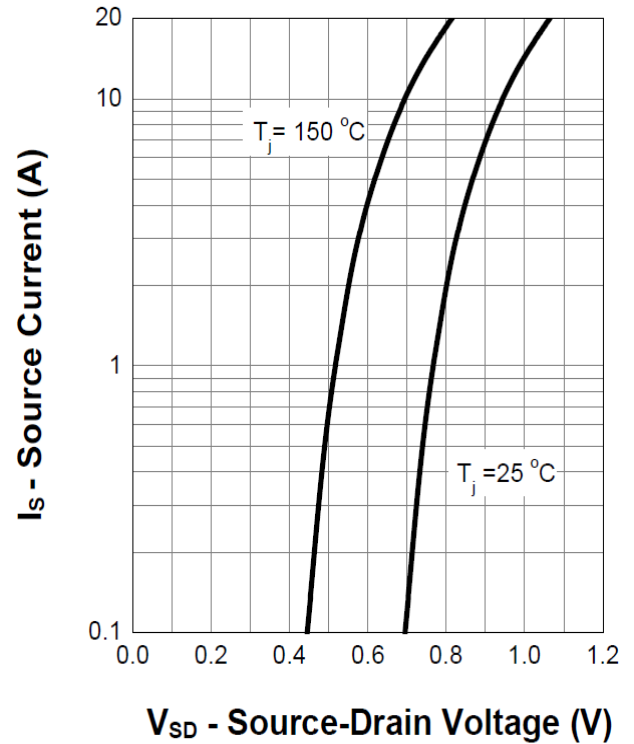


Electrical Characteristics Curves

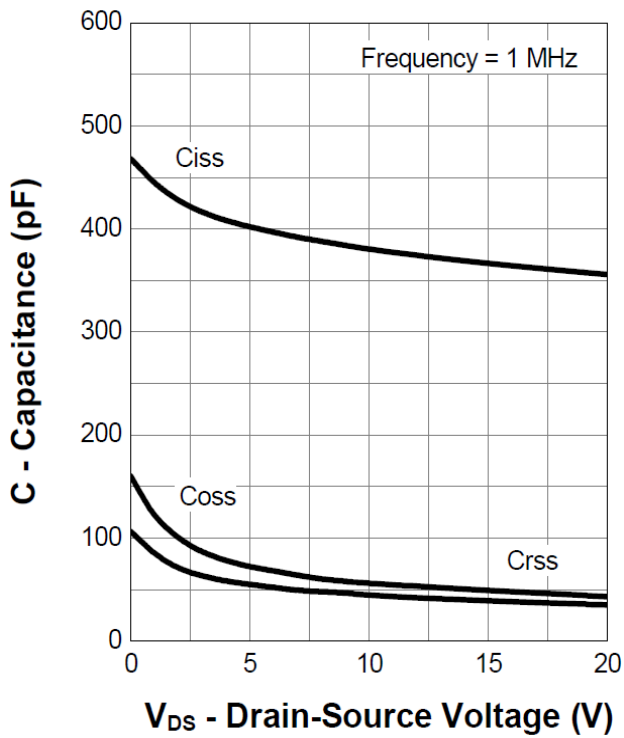
Normalized On Resistance



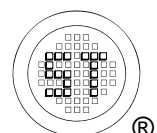
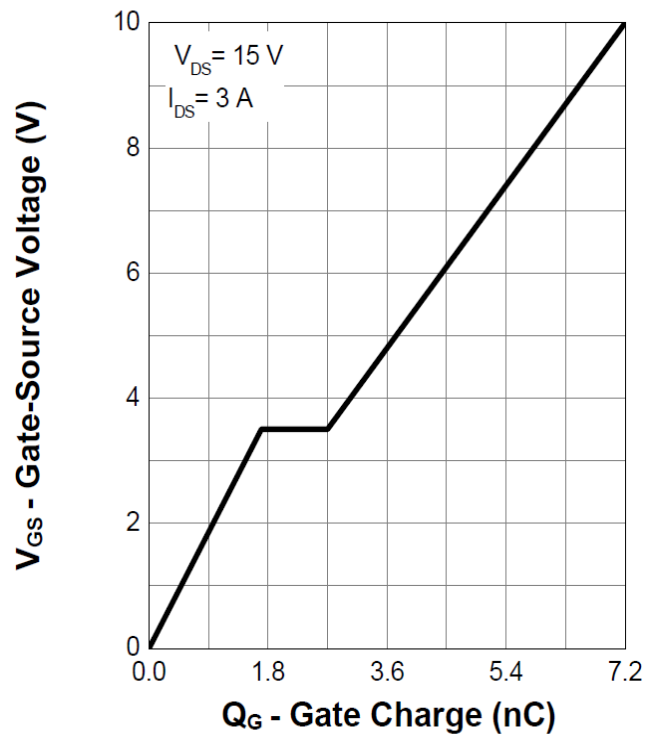
Diode Forward Current



Capacitance



Gate Charge



Test Circuits

Fig.1-1 Switching times test circuit

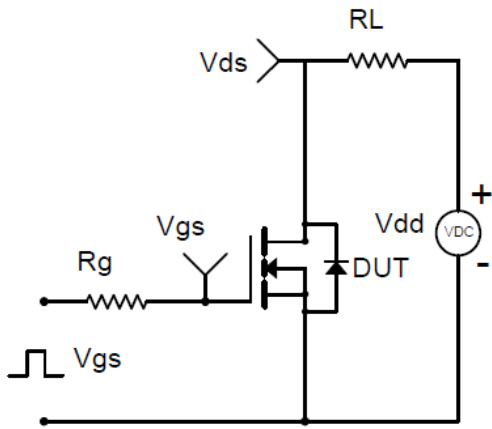


Fig.1-2 Switching Waveform

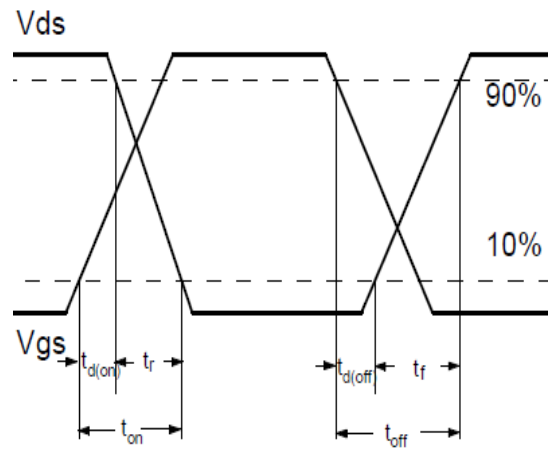


Fig.2-1 Gate charge test circuit

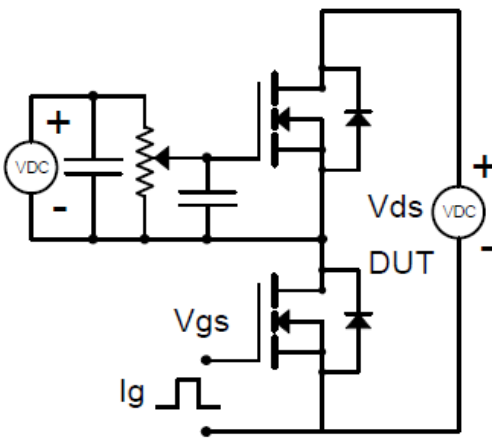
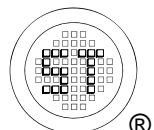
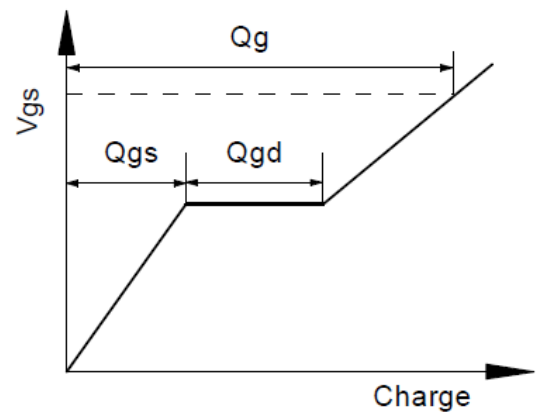


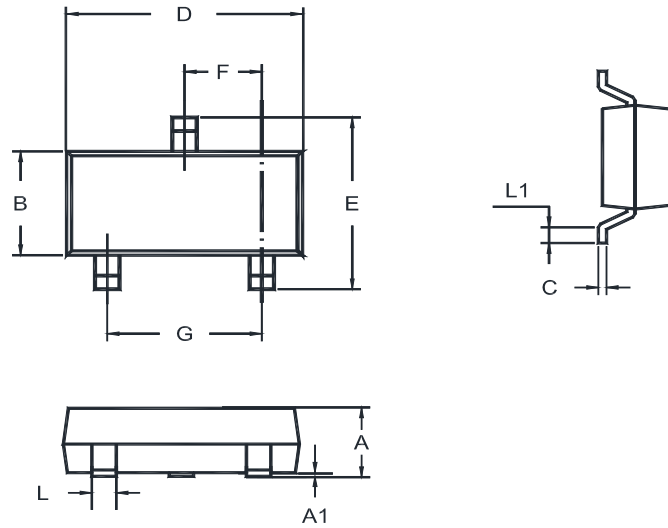
Fig.2-2 Gate charge waveform



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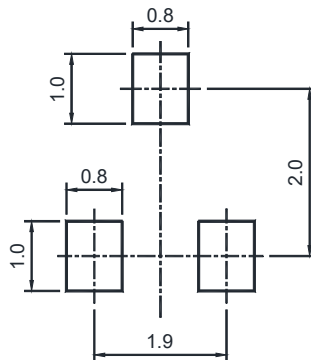
Package Outline (Dimensions in mm)

SOT-23



Unit	A	A1	B	C	D	E	F	G	L	L1
mm	1.20	0.100	1.40	0.19	3.04	2.6	1.02	2.04	0.51	0.2
	0.89	0.013	1.20	0.08	2.80	2.2	0.89	1.78	0.37	MIN

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-23	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

- " MW " = Part No.
 - " YM " = Date Code Marking
 - " Y " = Year
 - " M " = Month
- Font type: Arial

